



America Semiconductor

Silicon Super Fast Recovery Diode

**MUR20040CT thru
MUR20060CTR**
 $V_{RRM} = 50\text{ V} - 600\text{ V}$
 $I_F = 200\text{ A}$

Features

- High Surge Capability
- Types up to 600 V V_{RRM}

Twin Tower Package



Maximum ratings, at $T_j = 25\text{ }^\circ\text{C}$, unless otherwise specified ("R" devices have leads reversed)

Parameter	Symbol	Conditions	MUR20040CT (R)	MUR20060CT (R)	Unit
Repetitive peak reverse voltage	V_{RRM}		400	600	V
RMS reverse voltage	V_{RMS}		280	420	V
DC blocking voltage	V_{DC}		400	600	V
Continuous forward current	I_F	$T_C \leq 140\text{ }^\circ\text{C}$	200	200	A
Surge non-repetitive forward current, Half Sine Wave	$I_{F,SM}$	$T_C = 25\text{ }^\circ\text{C}$, $t_p = 8.3\text{ ms}$	400	400	A
Operating temperature	T_j		-40 to 175	-40 to 175	$^\circ\text{C}$
Storage temperature	T_{stg}		-40 to 175	-40 to 175	$^\circ\text{C}$

Electrical characteristics, at $T_j = 25\text{ }^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Conditions	MUR20040CT (R)	MUR20060CT (R)	Unit
Diode forward voltage	V_F	$I_F = 50\text{ A}$, $T_j = 25\text{ }^\circ\text{C}$	1.3	1.7	V
Reverse current	I_R	$V_R = 50\text{ V}$, $T_j = 25\text{ }^\circ\text{C}$	25	25	μA
		$V_R = 50\text{ V}$, $T_j = 125\text{ }^\circ\text{C}$	1	1	mA
Recovery Time					
Maximum reverse recovery time	T_{RR}	$I_F = 0.5\text{ A}$, $I_R = 1.0\text{ A}$, $I_{RR} = 0.25\text{ A}$	90	110	nS



